# 2SD1450

## Silicon NPN epitaxial planar type

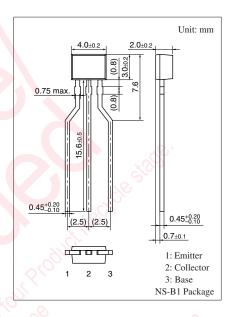
For low-frequency amplification

#### Features

- Optimum for high-density mounting
- Allowing supply with the radial taping
- $\bullet$  Low collector-emitter saturation voltage  $V_{\mbox{CE(sat)}}$

#### Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	25	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	20	V	
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	12	V	
Collector current	I <sub>C</sub>	0.5	Α	
Peak collector current	I <sub>CP</sub>	1	А	
Collector power dissipation	P <sub>C</sub>	300	mW	
Junction temperature	Tj	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	



#### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

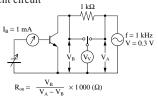
Parameter	Symbol	Conditions	Min	Тур	Max	🕑 Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = 10 \ \mu {\rm A}, I_{\rm E} = 0$	25		X0).	V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = 1 \text{ mA}, I_{\rm B} = 0$	20	a de	0.	ν
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	$I_{\rm E} = 10 \ \mu A, I_{\rm C} = 0$	12	XO	0.5	V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = 25 \text{ V}, I_E = 0$	<i>. K</i>	2	100	nA
Forward current transfer ratio *1	h <sub>FE1</sub> *2	$V_{CE} = 2 V, I_C = 0.5 A$	200	201	800	_
	h <sub>FE2</sub>	$V_{CE} = 2 V, I_C = 1 A$	60	0		
Collector-emitter saturation voltage *1	V <sub>CE(sat)</sub>	$I_{\rm C} = 500 \text{ mA}, I_{\rm B} = 20 \text{ mA}$	20°	0.13	0.40	V
Base-emitter saturation voltage *1	V <sub>BE(sat)</sub>	$I_{\rm C} = 500 \text{ mA}, I_{\rm B} = 20 \text{ mA}$			1.2	V
Transition frequency	f <sub>T</sub>	$V_{CB} = 10 \text{ V}, I_E = -50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		10		pF
(Common base, input open circuited)		in the second				
ON resistance *3	R <sub>on</sub>	MB 1/2		0.6		Ω

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

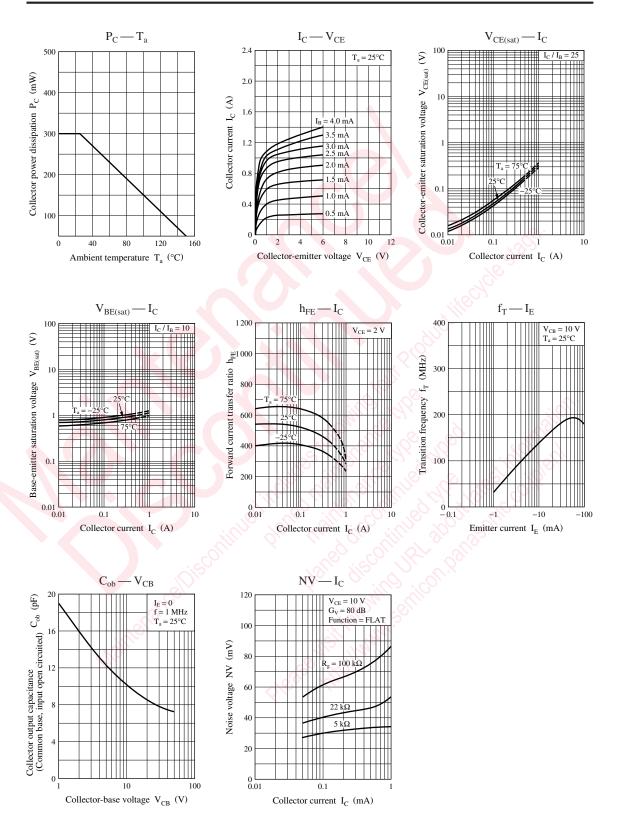
2. \*1: Pulse measurement

*	*2: Rank classification								
	Rank	R	S	Т	No rank				
	h <sub>FE1</sub>	200 to 350	300 to 500	400 to 800	200 to 800				

\*3: R<sub>on</sub> Measurement circuit



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